

Silicon Carbide Diode

Rev.01 - 30 May 2023

### **Product data sheet**

## 1. General description

Dual Silicon Carbide Schottky diode in a TO247 plastic package, designed for high frequency switched-mode power supplies.

## 2. Features and benefits

- New 6th Generation Technology
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- High Forward Surge Capability I<sub>FSM</sub>
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- AEC-Q101 qualified

### 3. Applications

- Power factor correction
  - Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives
- On board charger

## 4. Quick reference data

Symbol	Parameter	Conditions	Notes	Notes Values			
Absolute	maximum rating						-
$V_{\text{RRM}}$	repetitive peak reverse voltage				650		V
I <sub>O(AV)</sub>	limiting average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 133 °C; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>			A		
T <sub>j</sub>	junction temperature			-55 to 175			°C
Symbol	Parameter	Conditions	Notes	Min Typ Max			Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 5</u>		-	1.26	1.40	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 5</u>		-	1.35	1.55	V
Dynamic	characteristics						1
Q <sub>r</sub>	recovered charge	I <sub>F</sub> = 10 A; dI <sub>F</sub> /dt = 500 A/μs; V <sub>R</sub> = 400 V; T <sub>i</sub> = 25 °C; per diode; <u>Fig. 7</u>		-	24	-	nC





# **5. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	К	cathode	Щ <sub>О</sub> Ц	
3	A2	anode		K
mb	mb	mounting base; connected to cathode		sym125

# 6. Ordering information

Table 3. Ordering information											
Type number	Package	Orderable part number	Packing	Small packing	Package	Package					
	name		method	quantity	version	issue date					
WNSC6D20650CW-A	TO247	WNSC6D20650CW-A6Q	Tube	30	SOT429	25-Mar-2013					

# 7. Marking

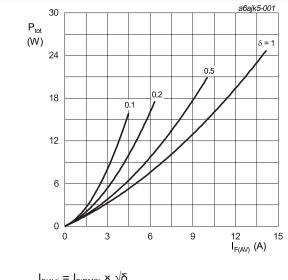
Table 4. Marking codes	
Type number	Marking codes
WNSC6D20650CW-A	WNSC6D 20650CW-A

# 8. Limiting values

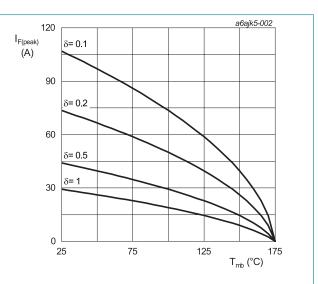
### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			650	V
$V_{\text{RWM}}$	crest working reverse voltage			650	V
V <sub>R</sub>	reverse voltage	DC		650	V
I <sub>O(AV)</sub>	limiting average forward current	δ = 0.5; square-wave pulse; T <sub>mb</sub> ≤ 133 °C; both diodes conducting; <u>Fig. 1; Fig. 2; Fig. 3</u>		20	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 134 °C; square-wave pulse; per diode		20	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode		75	A
		$t_{\rm p}$ = 10 µs; $T_{j(\text{init})}$ = 25 °C; square-wave pulse; per diode		800	A
l <sup>2</sup> t	l <sup>2</sup> t for fusing	sine-wave pulse; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms		28.125	A <sup>2</sup> s
T <sub>stg</sub>	storage temperature			-55 to 175	°C
T <sub>j</sub>	junction temperature			-55 to 175	°C



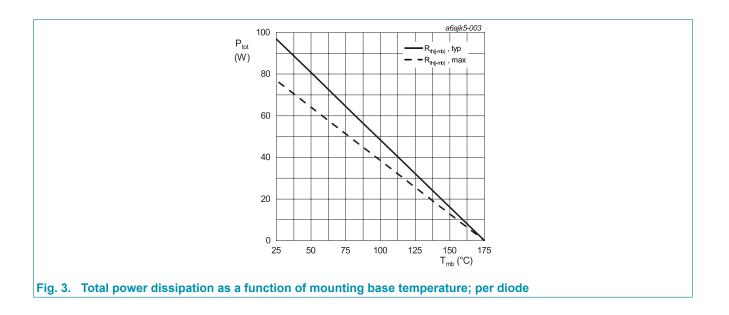
I<sub>F(AV)</sub> = I<sub>F(RMS)</sub> × √δ
V<sub>o</sub> = 0.910 V; R<sub>s</sub> = 0.0588 Ω
Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode





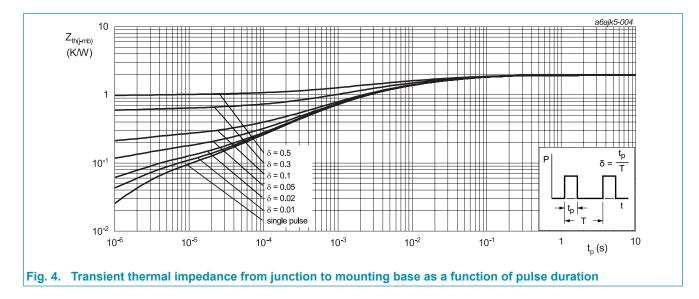
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## WNSC6D20650CW-A Silicon Carbide Diode



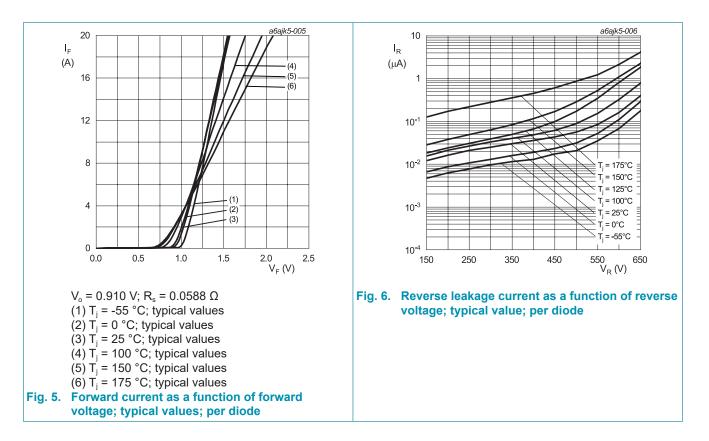
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance	per diode; <u>Fig. 4</u>		-	1.55	1.95	K/W
	from junction to mounting base	both diodes conducting		-	0.8	1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	40	-	K/W

# 9. Thermal characteristics



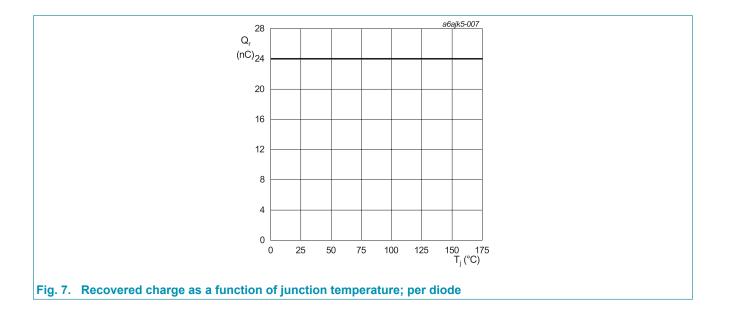
## **10. Characteristics**

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics						
V <sub>F</sub>	forward current	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 5</u>		-	1.26	1.40	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 5</u>		-	1.35	1.55	V
		$I_F = 10 \text{ A}; T_j = 175 \text{ °C}; \text{ per diode}; Fig. 5$		-	1.40	1.60	V
I <sub>R</sub> reverse current		urrent $V_R = 650 \text{ V}; \text{ T}_j = 25 \text{ °C}; \text{ per diode}; \text{Fig. 6}$			1	50	μA
		$V_{R}$ = 650 V; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 6</u>		-	15	200	μA
Dynamic	characteristics	-					
Q <sub>r</sub>	recovered charge	I <sub>F</sub> = 10 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 500 A/μs; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 7</u>		-	24	-	nC
C <sub>d</sub>	diode capacitance	f = 1 MHz; $V_R$ = 1 V; $T_j$ = 25 °C; per diode		-	500	-	pF
		f = 1 MHz; $V_R$ = 300 V; $T_j$ = 25 °C; per diode		-	58	-	pF
		f = 1 MHz; $V_R$ = 600 V; $T_j$ = 25 °C; per diode		-	52	-	pF
E <sub>as</sub>	non-repetitive avalanche energy	$I_R$ = 5 A; L = 5 mH; $T_{j(init)}$ = 25 °C; per diode		60	-	-	mJ



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Silicon Carbide Diode



# 11. Package outline

lastic single-ende	ed thr	ough	1-hole	pack	age;	heats	ink m	ount	ed; 1	mount	ing h	ole; 3	-lead	то-2	47					SOT42		
					• E	2- 2 3		-				20 г										
Dimensions (mm are	e the o	riginal	l dimen	isions)	1				SCa	ale												
							D.	De		E.	Fo	Fo	e <sup>(1)</sup>	L		Po		0				
	A <sub>1</sub> 2.10	b 1.40	b <sub>1</sub> 2.20	b <sub>2</sub> 3.20	c 0.70	D	D <sub>1</sub>	D <sub>2</sub>	E	E <sub>1</sub> 14.22	E <sub>2</sub>				L <sub>1</sub>	P <sub>2</sub> 3.60	p 3 70	Q	q 6 18	Ø		
max 5.20 mm nom min 4.70													5.45			3.60						
Note							,					-		_								
1. Basic spacing bet	tween	center	rs.																so	t429_po		
Outline version		IEC	<u></u>		JED		eferenc		EITA						Europ			ls	Issue date			
		IEC	,		JED	-0		JE	-074						, -,-,-,-				4-09-1			

# WNSC6D20650CW-A

#### Silicon Carbide Diode

# 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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